850 nm VCSEL for GI POF Links

Ramana Murty

Broadcom Inc.

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GI-POF based Optical Links

- GI-POF A4j characteristics will be defined in IEC at 850 nm, and some guidance on bandwidth for longer wavelengths is expected
- Goal for 802.3dh is to develop a link specification that enables a wide array of component suppliers VCSEL, PD, IC, fiber, and optical elements
- This presentation is regarding reliability of 850 nm VCSELs

A previous presentation on 850 nm 25G VCSEL reliability Laura Giovane, <u>https://www.ieee802.org/3/cz/public/8 jun 2021/giovane 3cz 01 080621.pdf</u>

850 nm VCSEL

- 850 nm VCSEL-based 25G links have been in use since 2014
- When it comes to reliability, one should distinguish between two aspects: wear-out life of the device, and random failure
- <u>Wear-out life</u> is established by accelerated aging tests

Applications generally call for operation at either 70°C ambient or 85°C ambient. A minimum TT1%F of 10 years is required at these conditions [cw operation].

Random failure is caused by manufacturing defects that slip through production

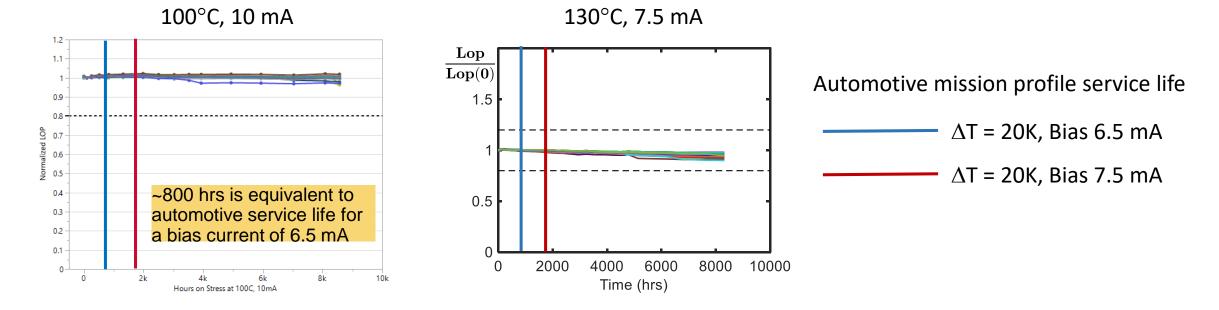
Field experience over 100M 25 GBd transceivers shows a random failure rate below 1 FIT.

- Automotive mission profile calls for a total operating lifetime of 32000 hrs (3.7 years) with a temperature profile (slides 5 and 9)
 - 105°C ambient 1% 100°C 8%

The automotive application is *adjacent* to the traditional high speed 850 nm VCSEL-based data links.

Accelerated Aging

- In estimating wear-out lifetime, a ΔT of 20K is assumed between ambient and VCSEL substrate
- Long term aging tests show that the <u>wear-out life</u> is several fold longer than automotive service life.



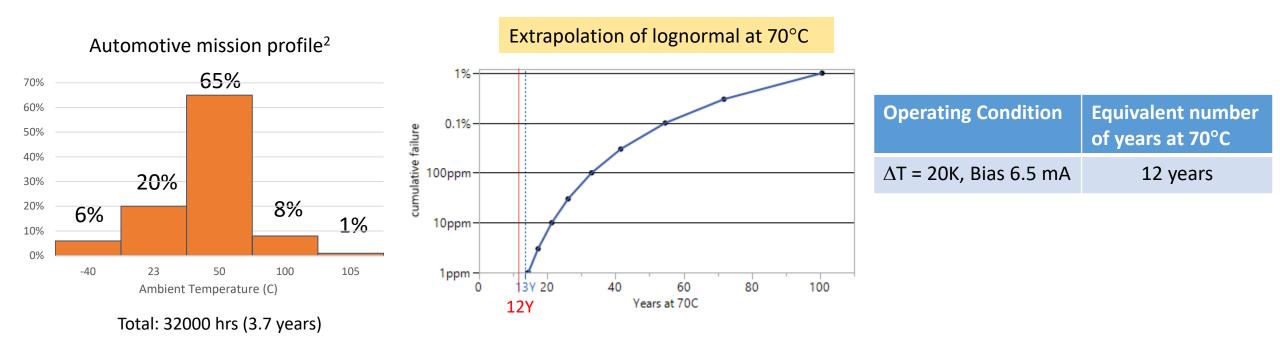
Literature on long lifetime for 25G and higher speed 850 nm VCSELs

M. Hoser et al., Highly Reliable 106 Gb/s PAM-4 850 nm Multi-Mode VCSEL for 800G Ethernet Applications, OFC 2022 Paper TuD2.5

N. Ledentsov, Jr., Technical feasibility and reliability of quantum-dot 850-nm VCSELs operating up to and above 25 Gbaud with a high temperature stability beyond 150°C, <u>https://www.ieee802.org/3/OMEGA/public/28 apr 2020/ledentsovJr OMEGA 01 280420 VCSEL.pdf</u>

Wear-out Lifetime

- Bias current of 6.5 mA is a sufficient for 25G operation at a VCSEL substrate temperature of 125°C.¹
- Automotive mission profile is translated to equivalent number of years operation at 70°C.
- 850 nm VCSEL wear-out life meets the requirement for automotive service.



1. Ramana Murty, https://www.ieee802.org/3/cz/public/sep_2021/murty_3cz_01_0921.pdf

2. R. King, https://www.ieee802.org/3/cz/public/nov_2020/king_3cz_01_1120.pdf

Failure Rate

850 nm 25 GBd VCSELs are widely deployed in data centers.

Field experience: Over 100M 850nm 25GBd VCSEL channels deployed for Data Centers

Field experience

< 1 DPPM (channel)

< 1 FIT (channel)

- Wear out failure mode is not observed in the field.
- Accelerated aging tests determine the parameters of the wear out failure mode.

Low random failure rate is more important in the field. How do you establish low random failure rate?

- 1. Failure modes have low activation energy; not easy to accelerate in a lab test (GR-468 Ea = 0.35 eV)
- 2. Demonstrating values below 10 FIT requires massive testing, or many years of field experience.

Summary

850 nm VCSELs have been proven in the field and are available today.

- 25 GBd VCSELs have sufficient wear-out lifetime to operate over the automotive temperature range.
- Low field FIT rate in data center applications over 8 years.
- Using 850 nm VCSELs for automotive application will leverage the established high volume, multi-vendor manufacturing eco-system.



Wear-out Life: A second mission profile

